## 505786831 11/22/2019

## PATENT ASSIGNMENT COVER SHEET

Electronic Version v1.1
Stylesheet Version v1.2

rsion v1.1 EPAS ID: PAT5833659

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT

#### **CONVEYING PARTY DATA**

Name	Execution Date
Shin-Chuan Huang	11/20/2019
Chih-Tung Yeh	11/20/2019
Chun-Ming Chang	11/20/2019
Bo-Rong Chen	11/20/2019
Wen-Jung Liao	11/20/2019
Chun-Liang Hou	11/20/2019

#### **RECEIVING PARTY DATA**

Name:	UNITED MICROELECTRONICS CORP.
Street Address:	No.3, Li-Hsin Road 2, Science-Based Industrial Park
City:	Hsin-Chu City
State/Country:	TAIWAN

### **PROPERTY NUMBERS Total: 1**

Property Type	Number
Application Number:	16691616

### **CORRESPONDENCE DATA**

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Email: Patent.admin.uspto.cr@naipo.com

Correspondent Name: WINSTON HSU

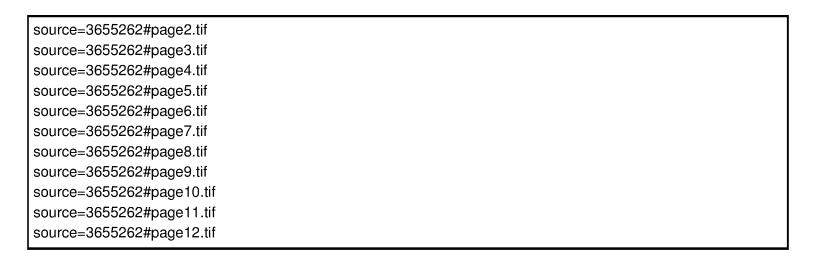
Address Line 1: 5F., NO.389, FUHE RD., YONGHE DIST.,

Address Line 4: NEW TAIPEI CITY, TAIWAN

ATTORNEY DOCKET NUMBER:	NAUP3534USA
NAME OF SUBMITTER:	SIBYL YU
SIGNATURE:	/SIBYL YU/
DATE SIGNED:	11/22/2019

**Total Attachments: 12** source=3655262#page1.tif

PATENT 505786831 REEL: 051083 FRAME: 0076



PATENT REEL: 051083 FRAME: 0077

### Title of Invention:

## HIGH ELECTRON MOBILITY TRANSISTOR AND FABRICATION METHOD THEREOF

As the below named inventor, I here This declaration is directed to:	by declare that:		
☑ The attached application, or			
☐ United States application nu	ımber	_filed on	, or
☐ PCT international applicatio	n number	filed on	1979
The above-identified application was	made or authorized to be made	by me.	
I believe that I am the original invent application.	or or an original joint inventor of a	a claimed invention ir	n the
I hereby acknowledge that any willfu under18 U.S.C. 1001 by fine or impr			le
In consideration of the payment by	UNITED MICROELECTROI	NICS having a po	ostal address of
No.3, Li-Hsin Road 2, Science	e-Based Industrial Park, Hs	in-Chu City 300,	Taiwan, R.O.C
(referred to as "ASSIGNEE"below) to acknowledged, andfor other good ar		00), the receipt of wh	ich is hereby
I hereby sell, assign and transfer to a the entire right, title and interest in a invention as above-identified applica invention by the above application of substitutes, or extensions thereof, an	nd to any and all improvements v ition and, in and to, all Letters Pa r any continuations, continuation-	which are disclosed in tent to be obtained fo in-part, divisions, rer	n the or said newals,
I hereby covenant that no assignment entered into which would conflict with		nce has been or will t	be made or
I further covenant that ASSIGNEE wand documents relating to said inver known and accessible to I and will te related thereto and will promptly exe	ntion and said Letters Patent and estify as to the same in any interfe	legal equivalents as erence, litigation prod	may be
representatives any and all papers, i maintain, issue and enforce said app equivalents thereof which may be ne IN WITNESS WHEREOF, I have he	olication, said invention and said lecessary or desirable to carry out	Letters Patent and sa the proposes thereo	f.
Note: An application data sheet (PTG	D/SB/14 or equivalent), including	naming the entire	

Page 1 of 12

inventive entity, must accompany this form. Use this form for each additional inventor.

NPO#NAU-P3534-USA:0 CUST#UMCD-2019-0505

LEGAL NAME OF INVENTOR(ASSIGNOR)

Inventor: Shin-Chuan Huang

Date:

NOV 2 0 2019

Signature:

Shin - Chuan

Huang

Page 2 of 12

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☐ United States application nu	ımber	filed on ,	
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The above-identified application was	s made or authorized to be made	by me.	
I believe that I am the original inventapplication.	or or an original joint inventor of	a claimed invention in	the
I hereby acknowledge that any willfu under18 U.S.C. 1001 by fine or impr	Il false statement made in this de isonment of not more than five (	eclaration is punishabl 5) years, or both.	e
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No.3, Li-Hsin Road 2, Science	e-Based Industrial Park, Hs	sin-Chu City 300, 7	Гаiwan, R.O.C
(referred to as "ASSIGNEE"below) to acknowledged, andfor other good are	o I of the sum of One Dollar (\$ 1 nd valuable consideration.	.00), the receipt of whi	ch is hereby
I hereby sell, assign and transfer to a the entire right, title and interest in a invention as above-identified applica- invention by the above application of substitutes, or extensions thereof, ar	nd to any and all improvements tion and, in and to, all Letters Pa r any continuations, continuation	which are disclosed in atent to be obtained fo -in-part, divisions, rene	the r said ewals
I hereby covenant that no assignment entered into which would conflict with	nt, sale, agreement or encumbra n this assignment;	nce has been or will b	e made or
I further covenant that ASSIGNEE w and documents relating to said inver known and accessible to I and will te related thereto and will promptly exe	ntion and said Letters Patent and estify as to the same in any interf	l legal equivalents as reference. litigation proce	may be
representatives any and all papers, i maintain, issue and enforce said app equivalents thereof which may be ne IN WITNESS WHEREOF, I have her	olication, said invention and said ecessary or desirable to carry ou	Letters Patent and sa	id
Note: An application data sheet (PTC	D/SB/14 or equivalent), including	naming the entire	

Page 3 of 12

inventive entity, must accompany this form. Use this form for each additional inventor.

NPO#NAU-P3534-USA:0 CUST#UMCD-2019-0505

LEGAL NAME OF INVENTOR(ASSIGNOR)

Inventor: Chih-Tung Yeh

Date:

NOV 2 0 2019

Signature:

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### Title of Invention:

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The above-identified application was	made or authorized to l	oe made by me.		
I believe that I am the original invent application.	or or an original joint inv	entor of a claimed	invention in the	
I hereby acknowledge that any willfu under18 U.S.C. 1001 by fine or impr				
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(referred to as "ASSIGNEE"below) to acknowledged, andfor other good an	o I of the sum of One Do nd valuable consideration	llar (\$ 1.00), the ro n.	eceipt of which is	hereby
I hereby sell, assign and transfer to A the entire right, title and interest in ar invention as above-identified applica invention by the above application or substitutes, or extensions thereof, ar	nd to any and all improve tion and, in and to, all Le any continuations, cont	ements which are etters Patent to be inuation-in-part, d	disclosed in the obtained for said ivisions, renewal	d s.
I hereby covenant that no assignmer entered into which would conflict with	nt, sale, agreement or er n this assignment;	ncumbrance has b	een or will be ma	ade or
I further covenant that ASSIGNEE w and documents relating to said inven- known and accessible to I and will te related thereto and will promptly exe-	ition and said Letters Pa stify as to the same in a	tent and legal equ ny interference, lit	ivalents as mav	be
representatives any and all papers, i maintain, issue and enforce said app equivalents thereof which may be ne IN WITNESS WHEREOF, I have her	olication, said invention a ecessary or desirable to	and said Letters Parry out the prop	atent and said oses thereof.	
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Page 5 of 12

inventive entity, must accompany this form. Use this form for each additional inventor.

NPO#NAU-P3534-USA:0 CUST#UMCD-2019-0505

LEGAL NAME OF INVENTOR(ASSIGNOR)			
Inventor:	Chun-Ming Chang	Date:	NOV 2 0 2019
Signature:	Chun-Ming Chang		

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NPO#NAU-P3534-USA:0 CUST#UMCD-2019-0505

### Title of Invention:

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☐ PCT international application number	filed on	
The above-identified application was made or authorize	d to be made by me.	
I believe that I am the original inventor or an original joir application.	nt inventor of a claimed invention in the	
I hereby acknowledge that any willful false statement m under18 U.S.C. 1001 by fine or imprisonment of not mo	ade in this declaration is punishable re than five (5) years, or both.	
In consideration of the payment by UNITED MICRO CORP.	DELECTRONICS having a postal ac	ddress of
No.3, Li-Hsin Road 2, Science-Based Industri	al Park, Hsin-Chu City 300, Taiwa	an, R.O.0
(referred to as "ASSIGNEE"below) to I of the sum of On acknowledged, andfor other good and valuable conside	e Dollar (\$ 1.00), the receipt of which is fration.	nereby
I hereby sell, assign and transfer to ASSIGNEE and the the entire right, title and interest in and to any and all im invention as above-identified application and, in and to, invention by the above application or any continuations, substitutes, or extensions thereof, and as to Letters Pate	provements which are disclosed in the all Letters Patent to be obtained for said continuation-in-part, divisions, renewals.	
I hereby covenant that no assignment, sale, agreement entered into which would conflict with this assignment;	or encumbrance has been or will be mad	de or
I further covenant that ASSIGNEE will, upon its request, and documents relating to said invention and said Letter known and accessible to I and will testify as to the same related thereto and will promptly execute and deliver to a	rs Patent and legal equivalents as may be in any interference. Iitigation proceeding	е
representatives any and all papers, instruments or affidamaintain, issue and enforce said application, said inventequivalents thereof which may be necessary or desirable IN WITNESS WHEREOF, I have hereunto set hand and	tion and said Letters Patent and said e to carry out the proposes thereof.	

Page 7 of 12

Note: An application data sheet (PTO/SB/14 or equivalent), including naming the entire inventive entity, must accompany this form. Use this form for <u>each additional inventor.</u>

LEGAL NAME OF INVENTOR(ASSIGNOR)				
Inventor:	Bo-Rong Chen	Date:	NOV 2 0 2019	
Signature:	Bo-Rong Chen			

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NPO#NAU-P3534-USA:0 CUST#UMCD-2019-0505

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NPO#NAU-P3534-USA:0 CUST#UMCD-2019-0505

ME OF INVENTOR(ASSIGNOR)			
Wen-Jung Liao	Date:	NOV 2 0 2019	
Wen-Jung Liao			
	Wen-Jung Liao	Wen-Jung Liao Date:	Wen-Jung Liao Date: NOV 2 0 2019

Page 10 of 12

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representatives any and all papers, i maintain, issue and enforce said app equivalents thereof which may be no IN WITNESS WHEREOF, I have her	olication, said invention and said ecessary or desirable to carry out	Letters Patent and the proposes ther	l said eof	
Note: An application data sheet (PTG	D/SB/14 or equivalent), including	naming the entire		

Page 11 of 12

inventive entity, must accompany this form. Use this form for each additional inventor.

NPO#NAU-P3534-USA:0 CUST#UMCD-2019-0505

Inventor: Chun-Liang Hou Date: NOV 2 0 2019

Signature: Chun-Liang flou

Page 12 of 12

F#NPO-P0002E-US1201 DSB0-108U031871

NPO#NAU-P3534-USA:0 CUST#UMCD-2019-0505

**RECORDED: 11/22/2019** 

PATENT REEL: 051083 FRAME: 0089